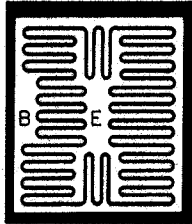


MEDIUM TO HIGH VOLTAGE, FAST SWITCHING

CHIP NUMBER

288



↑
.243"
(6.172mm)
↓

← .214"
(5.436mm) →

Base: .025" x .084" (0.64mm x 2.13mm)
Emitter: .024" x .084" (0.61mm x 2.13mm)

PNP EPITAXIAL PLANAR POWER TRANSISTOR**

CONTACT METALLIZATION

Base and emitter: > 50,000 Å Aluminum
Collector: Gold
(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .375" Diameter (9.53mm)
Thickness: .020" (0.51mm)

BeO PEDESTAL

Size: .250" x .312" (6.35mm x 7.93mm)
Thickness: .042" (1.07mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- a) the chip be eutectically mounted with gold silicon preform 98/2%.
- b) 12 mil (0.305mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 288 in a TO-3 or equivalent case:

V _{CEO}	V _{CE(s)} @	I _C	I _B	h _{FE} @	I _C	V _{CE}
> 60V	<1.0V	20A	2A	>15	30A	5V
> 80V	<1.0V	20A	2A	>15	30A	5V
>100V	<1.0V	20A	2A	>15	30A	5V
* >120V	<1.0V	20A	2A	>10	30A	5V
* >150V	<1.5V	20A	2A	>10	30A	5V

V _{CEO}	V _{CEX}	V _{EBO}	f _T	C _{OBO}	θ _{JC}
> 60V	70V	>5V	20MHz	<800pF	<0.8°C/W
> 80V	90V	>5V	20MHz	<800pF	<0.8°C/W
>100V	110V	>5V	20MHz	<800pF	<0.8°C/W
>120V	130V	>5V	20MHz	<800pF	<0.8°C/W
>150V	160V	>5V	20MHz	<800pF	<0.8°C/W

TYPICAL DEVICE TYPES: SDT6436 - SDT6438

*h_{FE} available at I_C = 20A, V_{CE} = 5V, >20

*The respective NPN complement is chip number 189.

